



30V, N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD17551Q5A

FEATURES

- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

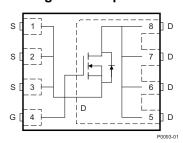
APPLICATIONS

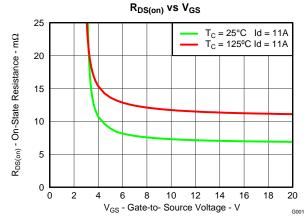
- Point of load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

DESCRIPTION

The NexFET power MOSFET has been designed to minimize losses in power conversion applications.

Figure 1. Top View





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage 30			
Q_g	Gate Charge Total (4.5V)	6.0	nC	
Q_{gd}	Gate Charge Gate to Drain	1.4	nC	
В	Drain to Source On Resistance	$V_{GS} = 4.5V$	9	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V 7		mΩ
V _{GS(th)}	Threshold Voltage	1.7	V	

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD17551Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V _{GS}	Gate to Source Voltage	±20	V
	Continuous Drain Current, T _C = 25°C	48	Α
I _D	Continuous Drain Current, T _A = 25°C ⁽¹⁾	13.5	Α
I_{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	85	Α
P_D	Power Dissipation ⁽¹⁾	3	W
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 25A$, $L = 0.1mH$, $R_G = 25\Omega$	31.3	mJ

(1) Typical $R_{\theta JA}=41.9^{\circ}\text{C/W}$ on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

GATE CHARGE

(2) Pulse duration ≤300µs, duty cycle ≤2%

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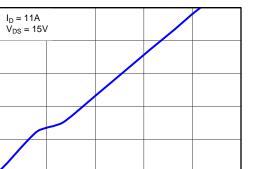
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6

0

0

V_{GS} - Gate-to-Source Voltage (V)



Q_g - Gate Charge - nC (nC)

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics	·				
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 24V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = 20V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.2	1.7	2.2	V
В	Drain to Source On Begintance	V _{GS} = 4.5V, I _D = 11A		9	11	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V, I _D = 11A		7	8.8	mΩ
9 _{fs}	Transconductance	V _{DS} = 15V, I _D = 11A		107		S
Dynamic	c Characteristics		·			
C _{iss}	Input Capacitance			1060	1272	pF
C _{oss}	Output Capacitance	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		247	296	pF
C _{rss}	Reverse Transfer Capacitance			19	24	pF
R _G	Series Gate Resistance			1.4	1.9	Ω
Qg	Gate Charge Total (4.5V)			6	7.2	nC
Q _{gd}	Gate Charge Gate to Drain	V 45V L 44A		1.4		nC
Q _{gs}	Gate to Source Threshold Voltage Drain to Source On Resistance Transconductance Drain to Source On Resistance Transconductance Drain to Source On Resistance Drain Capacitance Drain Capacitance Reverse Transfer Capacitance Geries Gate Resistance Gate Charge Total (4.5V) Gate Charge Gate to Drain Gate Charge Gate to Source Gate Charge at Vth Dutput Charge Turn On Delay Time Rise Time Turn Off Delay Time Fall Time acteristics Diode Forward Voltage Reverse Recovery Charge	$V_{DS} = 15V, I_{D} = 11A$		2.8		nC
Q _{g(th)}	Gate Charge at Vth			1.6		nC
Q _{oss}	Output Charge	V _{DS} = 13V, V _{GS} = 0V		7.2		nC
t _{d(on)}	Turn On Delay Time			9.1		ns
t _r	Rise Time	$V_{DS} = 15V, V_{GS} = 4.5V,$		15.5		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 11A$, $R_G = 2\Omega$		11.9		ns
t _f	Fall Time			4.3		ns
Diode C	haracteristics					
V _{SD}	Diode Forward Voltage	$I_{SD} = 11A, V_{GS} = 0V$		0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DS} = 13.5V, I _F = 11A,		8.7		nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/µs		13.5		ns

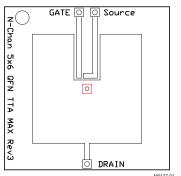
THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

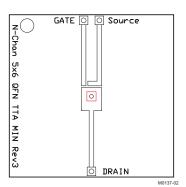
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			4.2	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			52.3	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 52.3^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 133^{\circ} C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

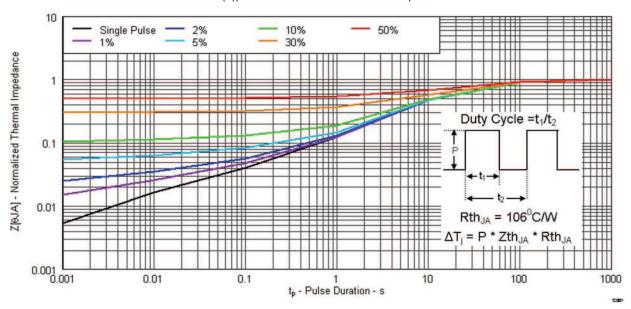


Figure 2. Transient Thermal Impedance

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TEXAS INSTRUMENTS

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

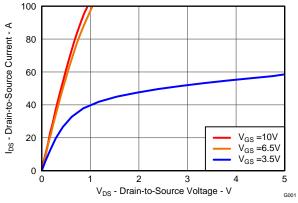


Figure 3. Saturation Characteristics

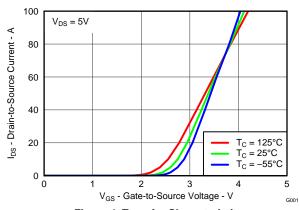


Figure 4. Transfer Characteristics

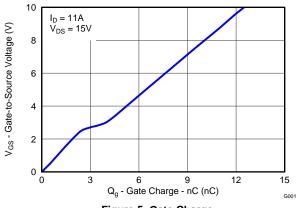


Figure 5. Gate Charge

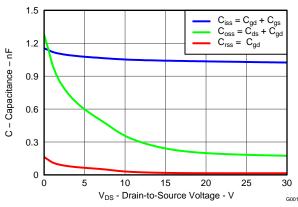


Figure 6. Capacitance

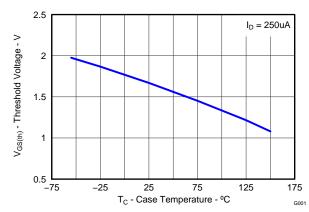


Figure 7. Threshold Voltage vs. Temperature

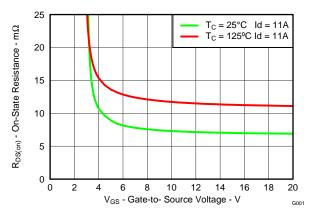


Figure 8. On-State Resistance vs. Gate-to-Source Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

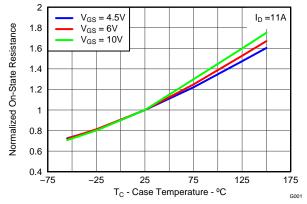


Figure 9. Normalized On-State Resistance vs. Temperature

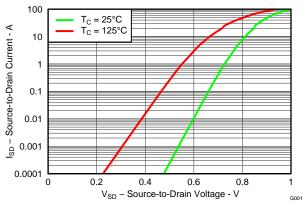


Figure 10. Typical Diode Forward Voltage

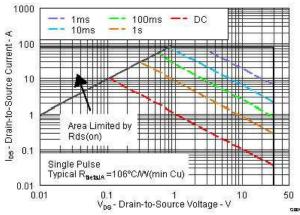


Figure 11. Maximum Safe Operating Area

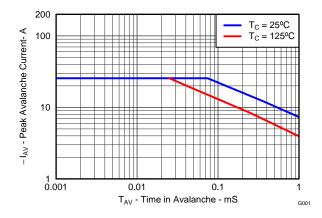


Figure 12. Single Pulse Unclamped Inductive Switching

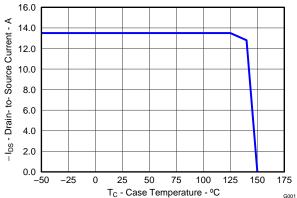
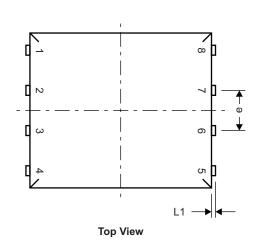


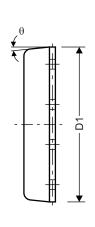
Figure 13. Maximum Drain Current vs. Temperature



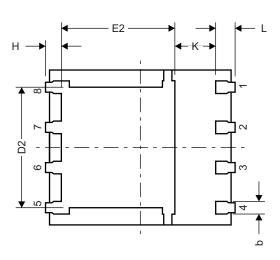
MECHANICAL DATA

Q5A Package Dimensions





Side View



Bottom View

F1 - -

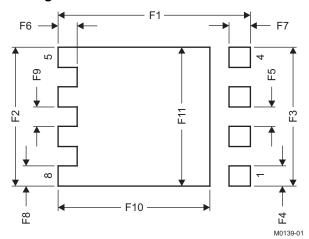
E Front View

M0135-01

DIM		MILLIMETERS	
DIW	MIN	NOM	MAX
А	0.90	1.00	1.10
b	0.33	0.41	0.51
С	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
Е	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
е	1.17	1.27	1.37
Н	0.41	0.56	0.71
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°



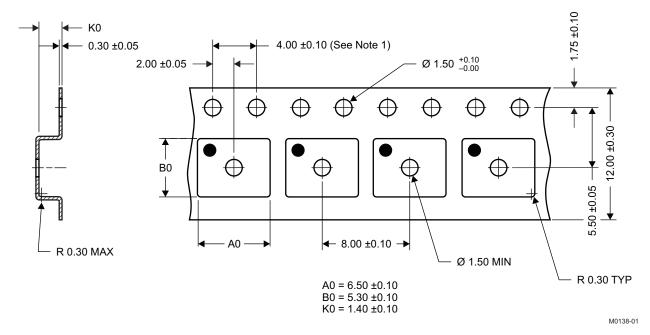
Figure 14. Recommended PCB Pattern



DIM	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5A Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket



PACKAGE OPTION ADDENDUM

11-Apr-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD17551Q5A	ACTIVE	VSON-FET	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD17551	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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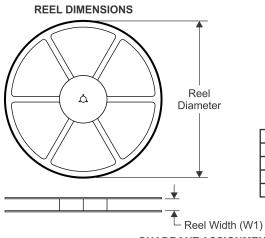


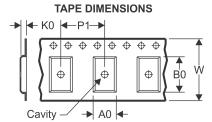
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PACKAGE MATERIALS INFORMATION

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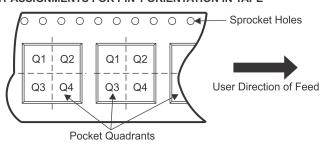
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17551Q5A	VSON- FET	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17551Q5A	VSON-FET	DQJ	8	2500	340.0	340.0	38.0

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